

Welcome to **E-XFL.COM**

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	Coldfire V1
Core Size	32-Bit
Speed	50.33MHz
Connectivity	I ² C, SCI, SPI, UART/USART
Peripherals	LVD, PWM, WDT
Number of I/O	36
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 9x12b SAR
Oscillator Type	External, Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mcf51ac128ccfge

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



1.1 Device Comparison

The MCF51AC256 series is summarized in Table 1.

Table 1. MCF51AC256 Series Device Comparison

Feature		AC256A	МС	MCF51AC256B			AC128A	MCF51AC128C		
reature	80-pin	64-pin	80-pin	64-pin	44-pin	80-pin	64-pin	80-pin	64-pin	44-pin
Flash memory size (Kbytes)			256				I	128	I	
RAM size (Kbytes)			32					32 or 16 ¹		
V1 ColdFire core with BDM (background debug module)	Yes									
ACMP1 (analog comparator)					١	⁄es				
ACMP2 (analog comparator)	Ye	es	Ye	es	No		Y	es		No
ADC (analog-to-digital converter) channels (12-bit)	24	20	24	20	9	24	20	24	20	9
CAN (controller area network)	Ye	es		No		Ye	es		No	
COP (computer operating properly)					١	⁄es				
CRC (cyclic redundancy check)					١	⁄es				
RTI	Yes									
DBG (debug)	Yes									
IIC1 (inter-integrated circuit)	Yes									
IRQ (interrupt request input)					١	⁄es				
INTC (interrupt controller)					١	⁄es				
KBI (keyboard interrupts)					١	⁄es				
LVD (low-voltage detector)					١	⁄es				
MCG (multipurpose clock generator)					١	/es				
OSC (crystal oscillator)					١	⁄es				
Port I/O ²	69	54	69	54	36	69	54	69	54	36
RGPIO (rapid general-purpose I/O)		1	6		12		1	6		12
SCI1, SCI2 (serial communications interfaces)	Yes									
SPI1 (serial peripheral interface)					١	⁄es				
SPI2 (serial peripheral interface)	Yes	No	Yes	N	lo	Yes	No	Yes	N	0
FTM1 (flexible timer module) channels		(3	1	4			6		4
FTM2 channels	6	2	6	2	2	6	2	6	2	2



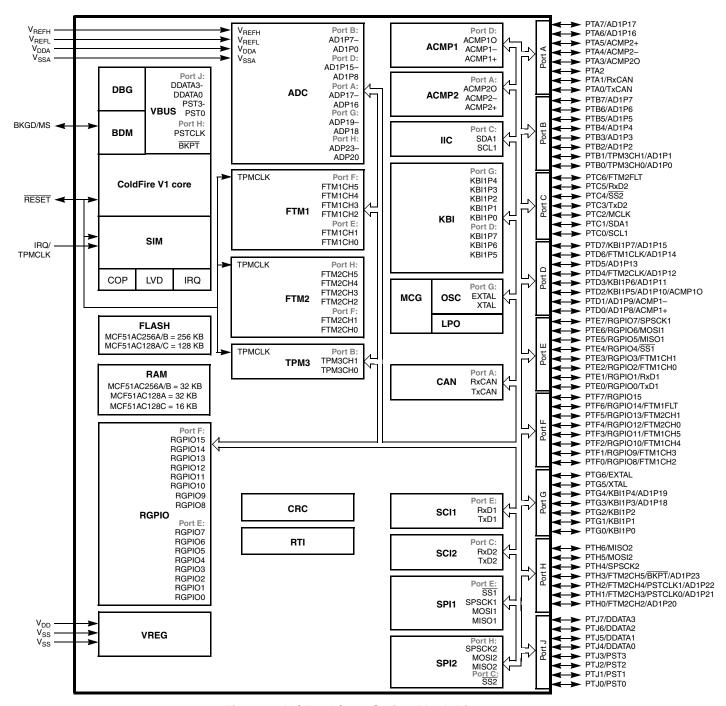


Figure 1. MCF51AC256 Series Block Diagram



- Trimmable internal reference allows 0.2% resolution and 2% deviation
- Analog-to-digital converter (ADC)
 - 24 analog inputs with 12 bits resolution
 - Output formatted in 12-, 10- or 8-bit right-justified format
 - Single or continuous conversion (automatic return to idle after single conversion)
 - Operation in low-power modes for lower noise operation
 - Asynchronous clock source for lower noise operation
 - Automatic compare with interrupt for less-than, or greater-than or equal-to, programmable value
 - On-chip temperature sensor
- Flexible timer/pulse-width modulators (FTM)
 - 16-bit Free-running counter or a counter with initial and final value. The counting can be up and unsigned, up and signed, or up-down and unsigned
 - Up to 6 channels, and each channel can be configured for input capture, output compare or edge-aligned PWM mode, all channels can be configured for center-aligned PWM mode
 - Channels can operate as pairs with equal outputs, pairs with complimentary outputs or independent channels (with independent outputs)
 - Each pair of channels can be combined to generate a PWM signal (with independent control of both edges of PWM signal)
 - Deadtime insertion is available for each complementary pair
 - The load of the FTM registers which have write buffer can be synchronized; write protection for critical registers
 - Generation of the triggers to ADC (hardware trigger)
 - A fault input for global fault control
 - Backwards compatible with TPM
- Timer/pulse width modulator (TPM)
 - 16-bit free-running or modulo up/down count operation
 - Two channels, each channel may be input capture, output compare, or edge-aligned PWM
 - One interrupt per channel plus terminal count interrupt
- Cyclic redundancy check (CRC) generator
 - High speed hardware CRC generator circuit using 16-bit shift register
 - CRC16-CCITT compliancy with $x^{16} + x^{12} + x^5 + 1$ polynomial
 - Error detection for all single, double, odd, and most multi-bit errors
 - Programmable initial seed value
- Analog comparators (ACMP)
 - Full rail to rail supply operation
 - Selectable interrupt on rising edge, falling edge, or either rising or falling edges of comparator output
 - Option to compare to fixed internal bandgap reference voltage
 - Option to allow comparator output to be visible on a pin, ACMPxO



- Inter-integrated circuit (IIC)
 - Compatible with IIC bus standard
 - Multi-master operation
 - Software programmable for one of 64 different serial clock frequencies
 - Interrupt driven byte-by-byte data transfer
 - Arbitration lost interrupt with automatic mode switching from master to slave
 - Calling address identification interrupt
 - Bus busy detection
 - 10-bit address extension
- Controller area network (CAN)
 - Implementation of the CAN protocol Version 2.0A/B
 - Standard and extended data frames
 - Zero to eight bytes data length
 - Programmable bit rate up to 1 Mbps
 - Support for remote frames
 - Five receive buffers with FIFO storage scheme
 - Three transmit buffers with internal prioritization using a "local priority" concept
 - Flexible maskable identifier filter supports two full-size (32-bit) extended identifier filters, four 16-bit filters, or eight 8-bit filters
 - Programmable wakeup functionality with integrated low-pass filter
 - Programmable loopback mode supports self-test operation
 - Programmable listen-only mode for monitoring of CAN bus
 - Programmable bus-off recovery functionality
 - Separate signalling and interrupt capabilities for all CAN receiver and transmitter error states (warning, error passive, bus-off)
 - Internal timer for time-stamping of received and transmitted messages
- Serial communications interfaces (SCI)
 - Full-duplex, standard non-return-to-zero (NRZ) format
 - Double-buffered transmitter and receiver with separate enables
 - Programmable baud rates (13-bit modulo divider)
 - Interrupt-driven or polled operation
 - Hardware parity generation and checking
 - Programmable 8-bit or 9-bit character length
 - Receiver wakeup by idle-line or address-mark
 - Optional 13-bit break character generation / 11-bit break character detection
 - Selectable transmitter output polarity
- Serial peripheral interfaces (SPI)
 - Master or slave mode operation
 - Full-duplex or single-wire bidirectional option
 - Programmable transmit bit rate

MCF51AC256 ColdFire Microcontroller Data Sheet, Rev.7



Table 3. Orderable Part Number Summary

MCF51AC256ACPUE	MCF51AC256 ColdFire Microcontroller with CAN	256 / 32	64 LQFP	–40°C to 85°C
MCF51AC256BCPUE	MCF51AC256 ColdFire Microcontroller without CAN	256 / 32	64 LQFP	–40°C to 85°C
MCF51AC256BCFGE	MCF51AC256 ColdFire Microcontroller without CAN	256/32	44 LQFP	–40°C to 85°C
MCF51AC128ACFUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 QFP	–40°C to 85°C
MCF51AC128CCFUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 QFP	–40°C to 85°C
MCF51AC128ACLKE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	80 LQFP	–40°C to 85°C
MCF51AC128CCLKE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	80 LQFP	–40°C to 85°CC
MCF51AC128ACPUE	MCF51AC128 ColdFire Microcontroller with CAN	128 / 32	64 LQFP	–40°C to 85°C
MCF51AC128CCPUE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	64 LQFP	–40°C to 85°C
MCF51AC128CCFGE	MCF51AC128 ColdFire Microcontroller without CAN	128 / 16	44 LQFP	–40°C to 85°C



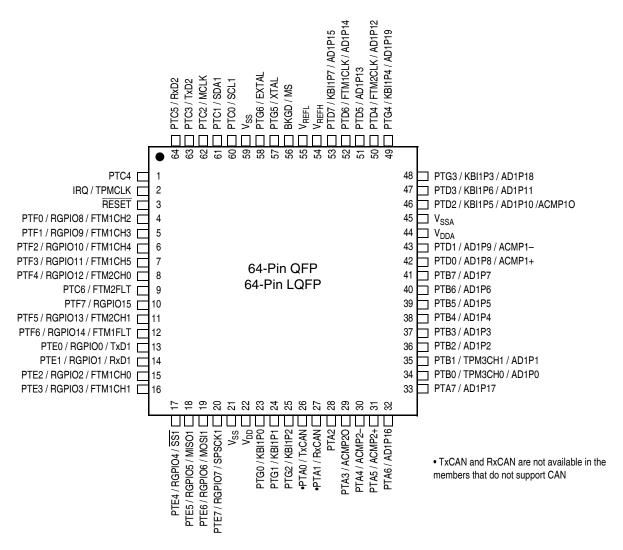


Figure 3. MCF51AC256 Series ColdFire Microcontroller 64-Pin QFP/LQFP

Figure 4 shows the pinout of the 44-pin LQFP.



Table 4. Pin Availability by Package Pin-Count (continued)

Pir	n Num	ber	Lowe	est < Pric	ority> Hi	ghest
80	64	44	Port Pin	Alt 1	Alt 2	Alt 3
8	8	6	PTF4	RGPIO12	FTM2CH0	
9	9	_	PTC6	FTM2FLT		
10	10	_	PTF7	RGPIO15		
11	11	7	PTF5	RGPIO13	FTM2CH1	
12	12	_	PTF6	RGPIO14	FTM1FLT	
13		_	PTJ0	PST0		
14		_	PTJ1	PST1		
15		_	PTJ2	PST2		
16		_	PTJ3	PST3		
17	13	8	PTE0	RGPIO0	TxD1	
18	14	9	PTE1	RGPIO1	RxD1	
19	15	10	PTE2	RGPIO2	FTM1CH0	
20	16	11	PTE3	RGPIO3	FTM1CH1	
21	17	12	PTE4	RGPIO4	SS1	
22	18	13	PTE5	RGPIO5	MISO1	
23	19	14	PTE6	RGPIO6	MOSI1	
24	20	15	PTE7	RGPI07	SPSCK1	
25	21	16	V_{SS}			
26	22	17	V_{DD}			
27	_	_	PTJ4	DDATA0		
28	_	_	PTJ5	DDATA1		
29	_	_	PTJ6	DDATA2		
30	_	_	PTJ7	DDATA3		
31	23	18	PTG0	KBI1P0		
32	24	19	PTG1	KBI1P1		
33	25	20	PTG2	KBI1P2		
34	26	21	PTA0	TxCAN ²		
35	27	22	PTA1	RxCAN ³		
36	28	_	PTA2			
37	29	_	PTA3	ACMP2O		
38	30	_	PTA4	ACMP2-		
39	31	_	PTA5	ACMP2+		
40	32	_	PTA6	AD1P16		
41	33	_	PTA7	AD1P17		
42	_	_	PTH0	FTM2CH2	AD1P20	
43	_	_	PTH1	FTM2CH3	PSTCLK0	AD1P21
44	_	_	PTH2	FTM2CH4	PSTCLK1	AD1P22
45	_	_	PTH3	FTM2CH5	BKPT	AD1P23
46	34	23	PTB0	TPM3CH0	AD1P0	
47	35	24	PTB1	TPM3CH1	AD1P1	
48	36	25	PTB2	AD1P2		

MCF51AC256 ColdFire Microcontroller Data Sheet, Rev.7



Table 4. Pin Availability by Package Pin-Count (continued)

Pir	n Num	ber	Low	est < Pric	ority> Hi	ighest
80	64	44	Port Pin	Alt 1	Alt 2	Alt 3
49	37	26	PTB3	AD1P3		
50	38	_	PTB4	AD1P4		
51	39	_	PTB5	AD1P5		
52	40	_	PTB6	AD1P6		
53	41	_	PTB7	AD1P7		
54	42	27	PTD0	AD1P8	ACMP1+	
55	43	28	PTD1	AD1P9	ACMP1-	
56	44	29	V_{DDA}			
57	45	30	V_{SSA}			
58	46	31	PTD2	KBI1P5	AD1P10	ACMP10
59	47	32	PTD3	KBI1P6	AD1P11	
60	48	33	PTG3	KBI1P3	AD1P18	
61	49	_	PTG4	KBI1P4	AD1P19	
62	50	_	PTD4	FTM2CLK	AD1P12	
63	51	_	PTD5	AD1P13		
64	52	_	PTD6	FTM1CLK	AD1P14	
65	53	_	PTD7	KBI1P7	AD1P15	
66	54	34	V_{REFH}			
67	55	35	V_{REFL}			
68	56	36	BKGD	MS		
69	57	37	PTG5	XTAL		
70	58	38	PTG6	EXTAL		
71	59	39	V_{SS}			
72	_	_	V_{DD}			
73	60	40	PTC0	SCL1		
74	61	41	PTC1	SDA1		
75			PTH4	SPCK2		
76			PTH5	MOSI2		
77			PTH6	MISO2		
78	62	42	PTC2	MCLK		
79	63	43	PTC3	TxD2		
80	64	44	PTC5	RxD2	_	

TPMCLK, FTM1CLK, and FTM2CLK options are configured via software; out of reset, FTM1CLK, FTM2CLK, and TPMCLK are available to FTM1, FTM2, and TPM3 respectively.

² TxCAN is available in the member that supports CAN.

³ RxCAN is available in the member that supports CAN.



Table 6. Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Supply voltage	V_{DD}	-0.3 to 5.8	V
Input voltage	V _{In}	$-0.3 \text{ to V}_{DD} + 0.3$	V
Instantaneous maximum current Single pin limit (applies to all port pins) ¹ , ² , ³	I _D	±25	mA
Maximum current into V _{DD}	I _{DD}	120	mA
Storage temperature	T _{stg}	-55 to 150	°C

Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V_{DD}) and negative (V_{SS}) clamp voltages, then use the larger of the two resistance values.

2.3 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and it is user-determined rather than being controlled by the MCU design. In order to take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 7. Thermal Characteristics

Rating		Symbol	Value	Unit
Operating temperature range (packaged)		T _A	-40 to 105	°C
Maximum junction temperature		TJ	150	°C
Thermal resistance 1,2,3,4				
80-pin LQFP	1s		51	
64-pin LQFP	2s2p		38 59	
64-pin QFP	2s2p	$\theta_{\sf JA}$	41 50	°C/W
44 pin LOED	1s 2s2p		36	
44-pin LQFP	1s 2s2p		67 45	

MCF51AC256 ColdFire Microcontroller Data Sheet, Rev.7

 $^{^{2}}$ All functional non-supply pins are internally clamped to V_{SS} and V_{DD} .

Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current (V_{In} > V_{DD}) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low which would reduce overall power consumption.



- Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance
- ² Junction to Ambient Natural Convection
- ³ 1s Single layer board, one signal layer
- ⁴ 2s2p Four layer board, 2 signal and 2 power layers

The average chip-junction temperature (T_I) in ${}^{\circ}C$ can be obtained from:

$$T_{J} = T_{A} + (P_{D} \times \theta_{JA})$$
 Eqn. 1

where:

 $T_A = Ambient temperature, °C$

 $\theta_{\rm JA}$ = Package thermal resistance, junction-to-ambient, °C/W

$$P_D = P_{int} + P_{I/O}$$

 $P_{int} = I_{DD} \times V_{DD}$, Watts — chip internal power

 $P_{I/O}$ = Power dissipation on input and output pins — user determined

For most applications, $P_{I/O} \ll P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_A + 273^{\circ}C)$$
 Eqn. 2

Solving Equation 1 and Equation 2 for K gives:

$$K = P_D \times (T_A + 273^{\circ}C) + \theta_{JA} \times (P_D)^2$$
 Eqn. 3

where K is a constant pertaining to the particular part. K can be determined from Equation 3 by measuring P_D (at equilibrium) for a known T_A . Using this value of K, the values of P_D and T_J can be obtained by solving Equation 1 and Equation 2 iteratively for any value of T_A .

2.4 Electrostatic Discharge (ESD) Protection Characteristics

Although damage from static discharge is much less common on these devices than on early CMOS circuits, normal handling precautions should be used to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with CDF-AEC-Q00 Stress Test Qualification for Automotive Grade Integrated Circuits. (http://www.aecouncil.com/) This device was qualified to AEC-Q100 Rev E.

A device is considered to have failed if, after exposure to ESD pulses, the device no longer meets the device specification requirements. Complete dc parametric and functional testing is performed per the



Table 10. DC Characteristics (continued)

Num	С	Parameter	Symbol	Min	Typical ¹	Max	Unit
		DC injection current ^{5 6 7 8} (single pin limit) $ V_{IN} > V_{DD} $ $ V_{IN} < V_{SS} $		0 0	_	2 -0.2	mA
22		DC injection current (Total MCU limit, includes sum of all stressed pins) $ \frac{V_{IN}>V_{DD}}{V_{IN}< V_{SS}} $	I _{IC}	0 0		25 -5	mA

Typical values are based on characterization data at 25°C unless otherwise stated.

- $^{6}\,$ All functional non-supply pins are internally clamped to V_{SS} and V_{DD} .
- Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.
- ⁸ The $\overline{\text{RESET}}$ pin does not have a clamp diode to V_{DD} . Do not drive this pin above V_{DD} .

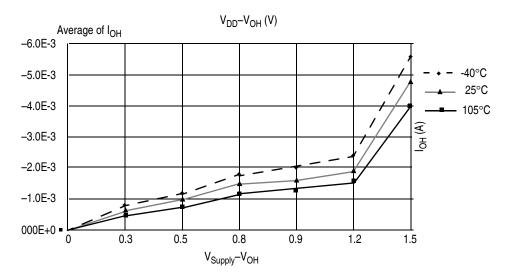


Figure 5. Typical I_{OH} vs. V_{DD}-V_{OH} at V_{DD} = 3 V (Low Drive, PTxDSn = 0)

² Measured with $V_{In} = V_{DD}$ or V_{SS} .

 $^{^{3}}$ Measured with $V_{In} = V_{SS}$.

⁴ Measured with $V_{In} = V_{DD}$.

Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current (V_{In} > V_{DD}) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if clock rate is very low (which would reduce overall power consumption).



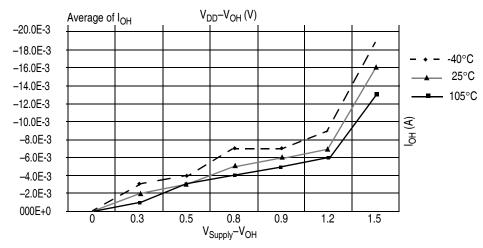


Figure 6. Typical I_{OH} vs. $V_{DD}-V_{OH}$ at $V_{DD}=3$ V (High Drive, PTxDSn = 1)

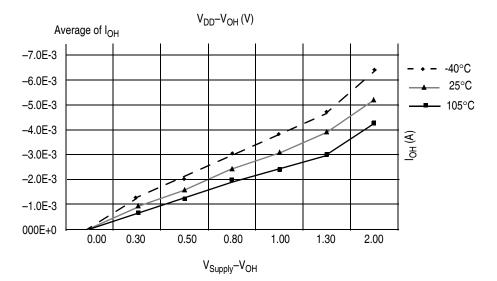


Figure 7. Typical I_{OH} vs. $V_{DD}-V_{OH}$ at $V_{DD}=5$ V (Low Drive, PTxDSn = 0)



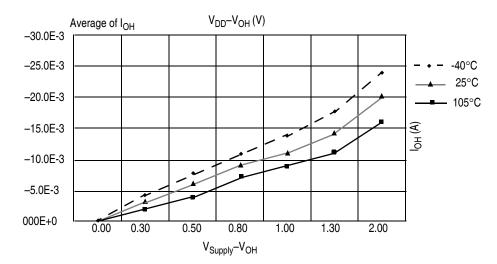


Figure 8. Typical I_{OH} vs. V_{DD} – V_{OH} at V_{DD} = 5 V (High Drive, PTxDSn = 1)



Table 11. Supply Current Characteristics (continued)

Num	С	Parameter	Symbol	V _{DD} (V)	Typical ¹	Max ²	Unit
5	С	Wait mode supply ³ current measured at	at		1.3	2	- mA
3		(CPU clock = 2 MHz, f _{Bus} = 1 MHz)		3	1.29	2	ША
6	C	Wait mode supply ³ current measured at	WI _{DD}	5	5.11	8	mA
		(CPU clock = 16 MHz, f _{Bus} = 8 MHz)	טטיייי	3	5.1	8	1117 (
7	С	Wait mode supply ³ current measured at		5	15.24	25	mA
,		(CPU clock = 50 MHz, f _{Bus} = 25 MHz)		3	15.2	25	1117
8	С	Stop2 mode supply current -40 °C 25 °C 120 °C	S2I _{DD}	5	1.40	2.5 2.5 200	μА
Ü		–40 °C 25 °C 120 °C	OZI _{DD}	3	1.16	2.5 2.5 200	μА
9	С	Stop3 mode supply current -40 °C 25 °C 120 °C	S3I _{DD}	5	1.60	2.5 2.5 220	μА
		–40 °C 25 °C 120 °C	· DD	3	1.35	2.5 2.5 220	μΑ
10	С	RTI adder to stop2 or stop3 ³ , 25 °C	S23I _{DDRTI}	5	300		nA
		1111 44401 to stope of stope , 20	OZOIDDRTI	3	300		nA
11	С	Adder to stop3 for oscillator enabled ⁴ (ERCLKEN =1 and EREFSTEN = 1)	S3I _{DDOSC}	5, 3	5		μА

¹ Typicals are measured at 25 °C.

² Values given here are preliminary estimates prior to completing characterization.

Most customers are expected to find that auto-wakeup from stop2 or stop3 can be used instead of the higher current wait mode

⁴ Values given under the following conditions: low range operation (RANGE = 0), low power mode (HGO = 0).



Table 14. 5 Volt 12-bit ADC Characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Num	С	Characteristic	Conditions	Symb	Min	Typical ¹	Max	Unit	Comment	
- 1		Conversion	Short sample (ADLSMP = 0)		_	20		ADCK	See	
7	Р	time (including sample time)	Long sample (ADLSMP = 1)	t _{ADC}	_	40	_	cycles	Table 10 for	
0	Т	Comple time	Short sample (ADLSMP = 0)		_	3.5	_	ADCK	conversion time	
8	'	Sample time	Long sample (ADLSMP = 1)	t _{ADS}	_	23.5		cycles	variances	
	Т	Total	12-bit mode		_	±3.0	_		Includes	
9	Р	Total unadjusted	10-bit mode	E _{TUE}	_	±1	±2.5	LSB ²	quantizatio	
	Т	error	8-bit mode		_	±0.5	±1.0		n	
	Т		12-bit mode		_	±1.75	_			
10	Р	Differential non-linearity	10-bit mode ³	DNL	_	±0.5	±1.0	LSB ²		
	Т		8-bit mode ³		_	±0.3	±0.5			
	Т		12-bit mode		_	±1.5	_			
11	Т	Integral non-linearity	10-bit mode	INL	_	±0.5	±1.0	LSB ²		
	Т	, , , ,	8-bit mode		_	±0.3	±0.5			
	Т		12-bit mode		_	±1.5	_			
12	Р	Zero-scale error	10-bit mode	E _{ZS}	_	±0.5	±1.5	LSB ²	V _{ADIN} = V _{SSA}	
	Т		8-bit mode		_	±0.5	±0.5		JOA	
	Т		12-bit mode		_	±1	_			
13	Р	Full-scale error	10-bit mode	E _{FS}	_	±0.5	±1	LSB ²	$V_{ADIN} = V_{DDA}$	
	Т		8-bit mode		_	±0.5	±0.5		DDA	
			12-bit mode		_	-1 to 0	_			
14	D	Quantization error	10-bit mode	EQ	_	_	±0.5	LSB ²		
			8-bit mode		_	_	±0.5			
			12-bit mode		_	±1	_		Pad	
15	D	Input leakage error	10-bit mode	E _{IL}	E _{IL} - ±0.2 ±2.5	E _{IL} — ±0.2 ±2.5 LS	LSB ²	leakage ⁴ *		
			8-bit mode		_	±0.1	±1		R _{AS}	
16	D	Temp sensor voltage	25°C	V _{TEMP25}	_	1.396	_	V		
17	D	Temp sensor	–40 °C–25 °C	m		3.266	3.266 —	mV/°C		
17	0	slope	25 °C–85 °C	m	_	3.638	_	IIIV/-C		

Typical values assume V_{DDA} = 5.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

MCF51AC256 ColdFire Microcontroller Data Sheet, Rev.7

² 1 LSB = $(V_{REFH} - V_{REFL})/2^N$.



Num	С	Rating	Symbol	Min	Typical ¹	Max	Unit
18	D	Lock exit frequency tolerance 8	D _{unl}	±4.47	_	±5.97	%
19	D	Lock time — FLL	t _{fll_lock}	_		t _{fll_acquire+} 1075(1/ ^f int_t)	S
20	D	Lock time — PLL	t _{pll_lock}	_	_	t _{pll_acquire+} 1075(1/ ^f pll_ref)	s
21	D	Loss of external clock minimum frequency — RANGE = 0	f _{loc_low}	(3/5) × f _{int}	_	_	kHz

¹ Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.

- ⁴ This specification applies when the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
- Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{BUS}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V_{DD} and V_{SS} and variation in crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.
- 625 ns represents 5 time quanta for CAN applications, under worst case conditions of 8 MHz CAN bus clock, 1 Mbps CAN bus speed, and 8 time quanta per bit for bit time settings. 5 time quanta is the minimum time between a synchronization edge and the sample point of a bit using 8 time quanta per bit.
- Below D_{lock} minimum, the MCG enters lock. Above D_{lock} maximum, the MCG will not enter lock. But if the MCG is already in lock, then the MCG may stay in lock.
- Below D_{unl} minimum, the MCG will not exit lock if already in lock. Above D_{unl} maximum, the MCG is guaranteed to exit lock.

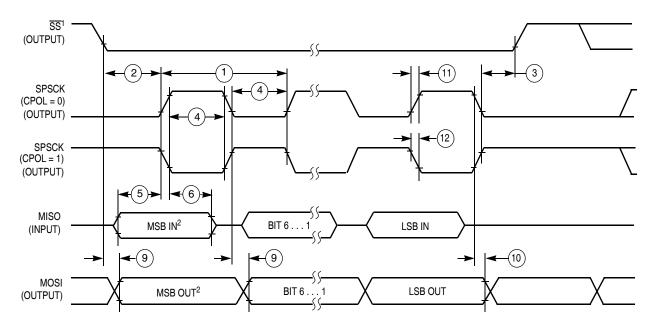
2.11 AC Characteristics

This section describes ac timing characteristics for each peripheral system.

² The resulting bus clock frequency must not exceed the maximum specified bus clock frequency of the device.

This specification applies when the FLL reference source or reference divider is changed, trim value changed or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

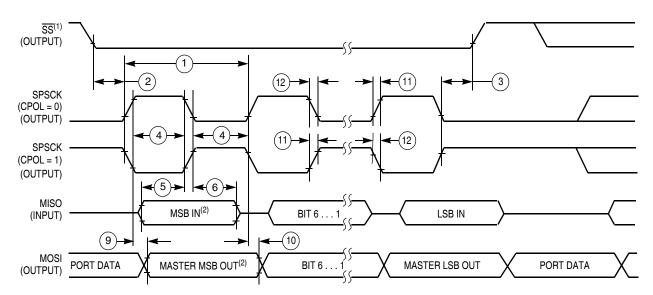




NOTES:

- 1. \overline{SS} output mode (DDS7 = 1, SSOE = 1).
- 2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 15. SPI Master Timing (CPHA = 0)

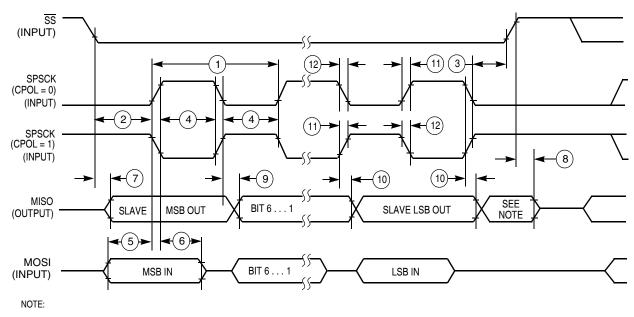


NOTES:

- 1. \overline{SS} output mode (DDS7 = 1, SSOE = 1).
- 2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

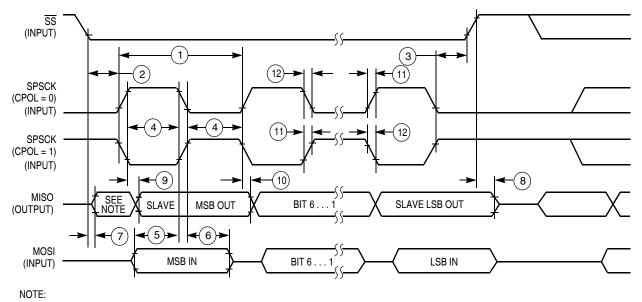
Figure 16. SPI Master Timing (CPHA =1)





1. Not defined but normally MSB of character just received

Figure 17. SPI Slave Timing (CPHA = 0)



1. Not defined but normally LSB of character just received

Figure 18. SPI Slave Timing (CPHA = 1)

2.13 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the Flash memory.

Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see Chapter 4, "Memory."



Num	С	Characteristic	Symbol	Min	Typical ¹	Max	Unit
1	_	Supply voltage for program/erase	V _{prog/erase}	2.7	_	5.5	V
2	_	Supply voltage for read operation	V _{Read}	2.7	_	5.5	V
3		Internal FCLK frequency ²	f _{FCLK}	150	_	200	kHz
4		Internal FCLK period (1/FCLK)	t _{Fcyc}	5	_	6.67	μS
5		Byte program time (random location) ²	t _{prog}	9			t _{Fcyc}
6		Byte program time (burst mode) ²	t _{Burst}	4			t _{Fcyc}
7		Page erase time ³	t _{Page}	4000			t _{Fcyc}
8		Mass erase time ²	t _{Mass}	20,000			t _{Fcyc}
9	O	Program/erase endurance ⁴ T_L to $T_H = -40$ °C to 105 °C $T = 25$ °C	_	10,000 —	 100,000		cycles
10	С	Data retention ⁵	t _{D_ret}	15	100	_	years

Table 21. Flash Characteristics

2.14 EMC Performance

Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

2.14.1 Radiated Emissions

Microcontroller radiated RF emissions are measured from 150 kHz to 1 GHz using the TEM/GTEM Cell method in accordance with the IEC 61967-2 and SAE J1752/3 standards. The measurement is performed with the microcontroller installed on a custom EMC evaluation board while running specialized EMC test software. The radiated emissions from the microcontroller are measured in a TEM cell in two package orientations (North and East). For more detailed information concerning the evaluation results, conditions and setup, please refer to the EMC Evaluation Report for this device.

¹ Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.

² The frequency of this clock is controlled by a software setting.

These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

Typical endurance for flash was evaluated for this product family on the 9S12Dx64. For additional information on how Freescale Semiconductor defines typical endurance, please refer to Engineering Bulletin EB619/D, Typical Endurance for Nonvolatile Memory.

Typical data retention values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25°C using the Arrhenius equation. For additional information on how Freescale Semiconductor defines typical data retention, please refer to Engineering Bulletin EB618/D, Typical Data Retention for Nonvolatile Memory.



4 Revision History

Table 23. Revision History

Revision	Description		
1	Initial published		
2	Updated ADC channels, Item 1, 4-5 on Table 2.10		
3	Completed all the TBDs. Changed RTC to RTI in Figure 1. Corrected the block diagram. Changed V_{DDAD} to V_{DDA} , V_{SSAD} to V_{SSA} . Added charge device model data and removed machine data in Table 8. Updated the specifications of V_{LVDH} , V_{LVDL} , V_{LVWH} and V_{LVWL} in Table 10. Updated $S2I_{DD}$, $S3I_{DD}$ in Table 11. Added C column in Table 14. Updated f_{dco_DMX32} in Table 16.		
4	Corrected the expansion of SPI to serial peripheral interface.		
5	Updated V _{LVDL} in the Table 10. Updated RI _{DD} in the Table 11.		
6	Updated V _{LVDH} , V _{LVDL} , V _{LVWH} and V _{LVWL} in the Table 10. Added LPO on the Figure 1 and LPO features in the Section 1.3, "Features."		
7	Added 44-pin LQFP package information for AC256 and AC128.		